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FIG. 2A

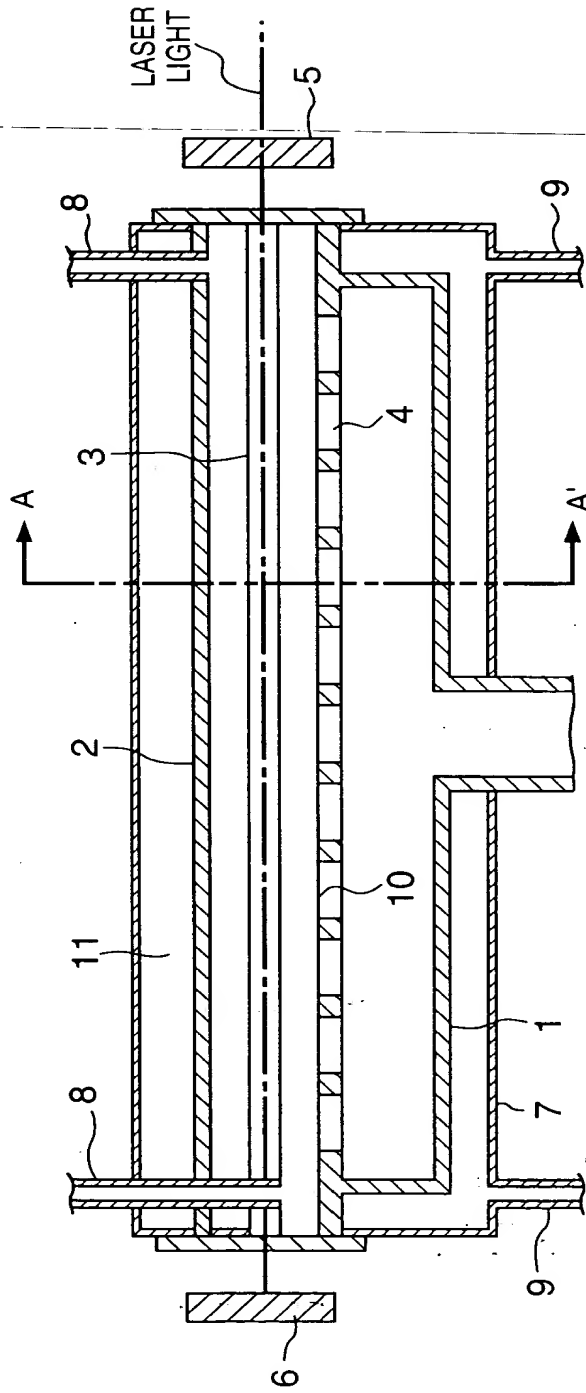


FIG. 2B

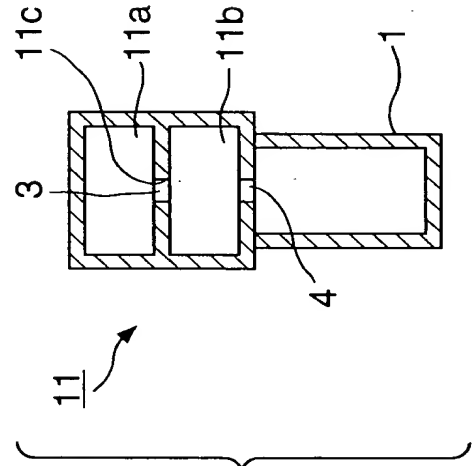
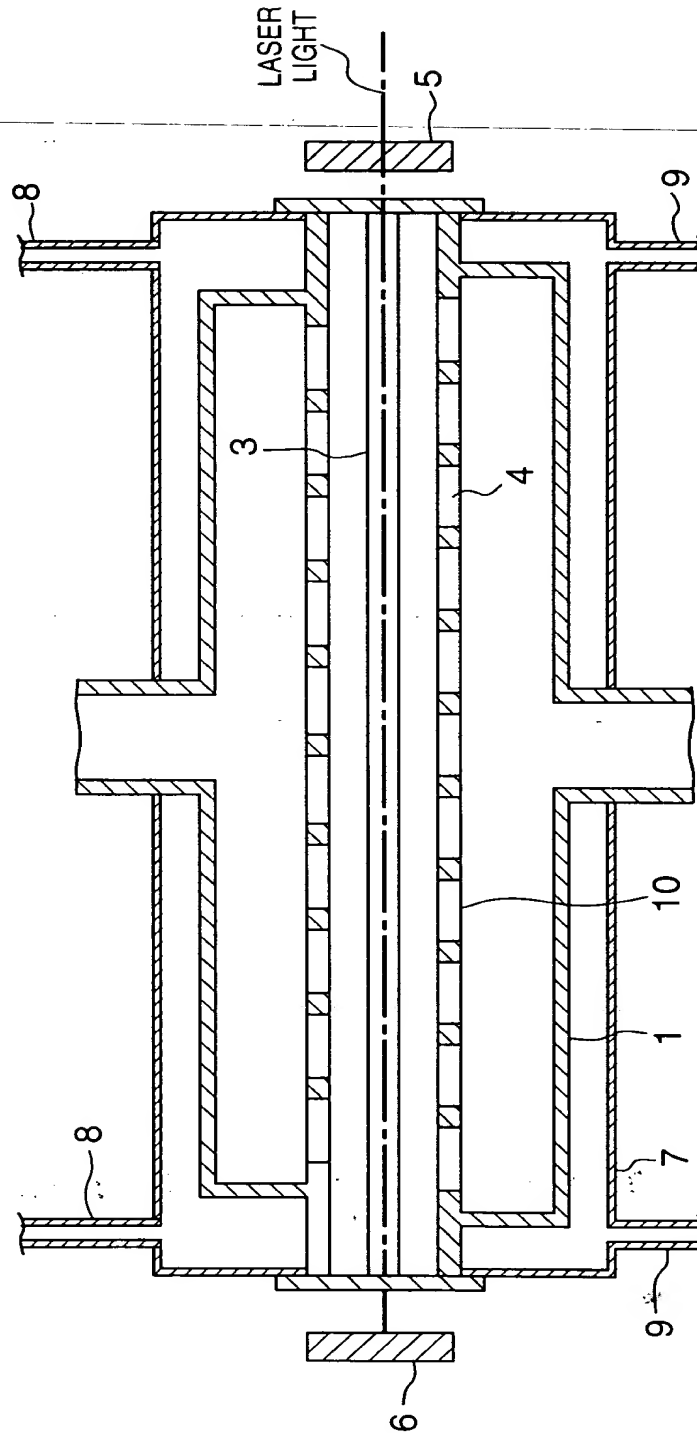


FIG. 3



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FIG. 4A

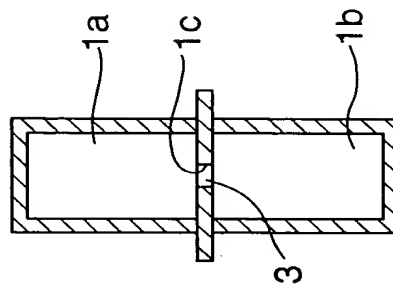
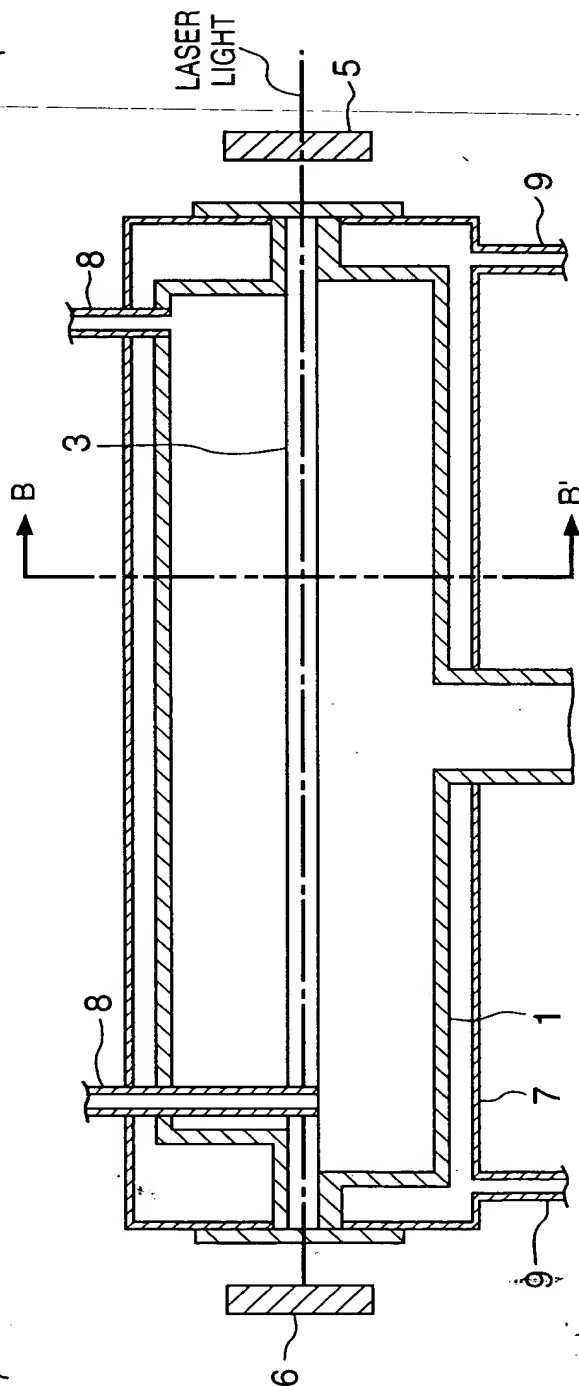


FIG. 4B

FIG. 5A

ACTION IN INPUT-SIDE WAVEGUIDE PLASMA

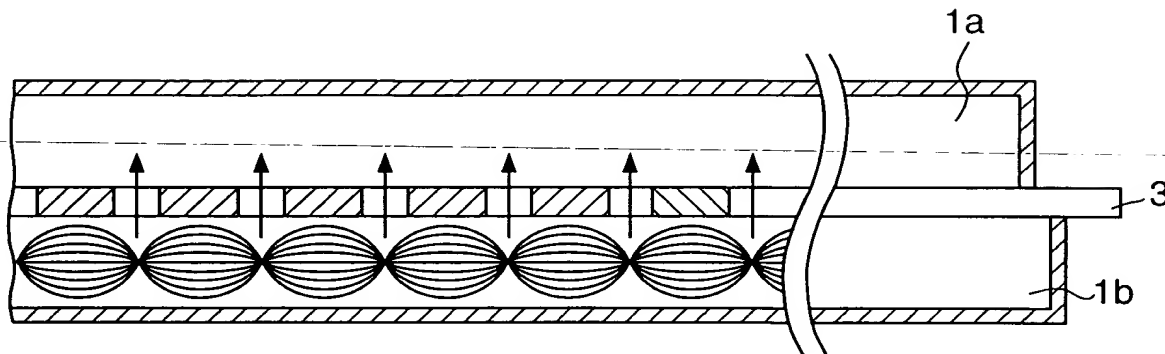


FIG. 5B

ACTION FROM PLASMA NON-EXCITED POSITIONS
STANDING WAVE IN RESONANCE WAVEGUIDE BY LEAKAGE TO WAVEGUIDE

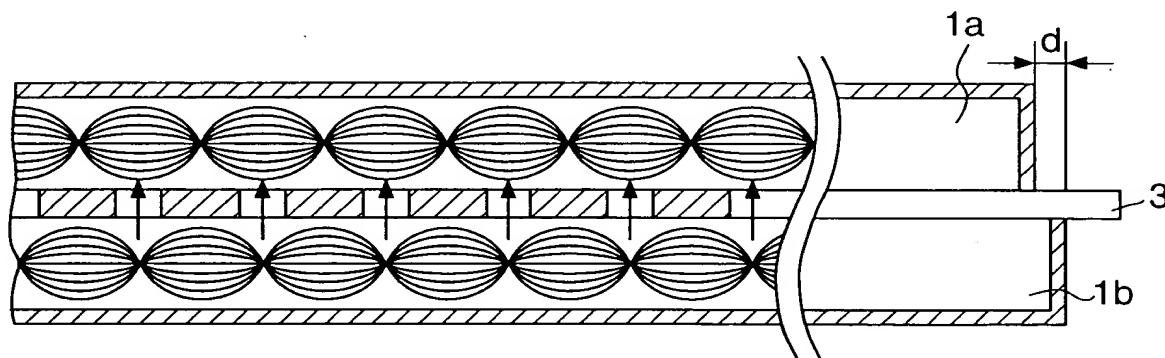
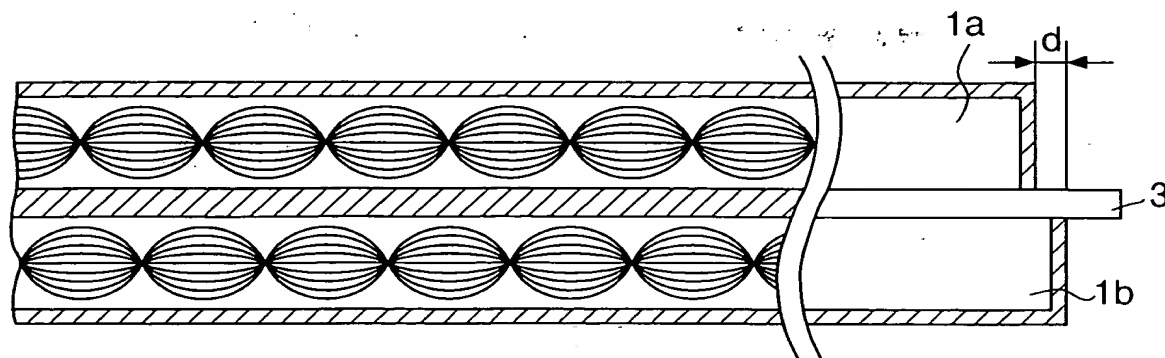


FIG. 5C

INTERPOLATION IN PLASMA
EXCITATION SPACE USING STANDING WAVE IN RESONANCE WAVEGUIDE



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FIG. 6

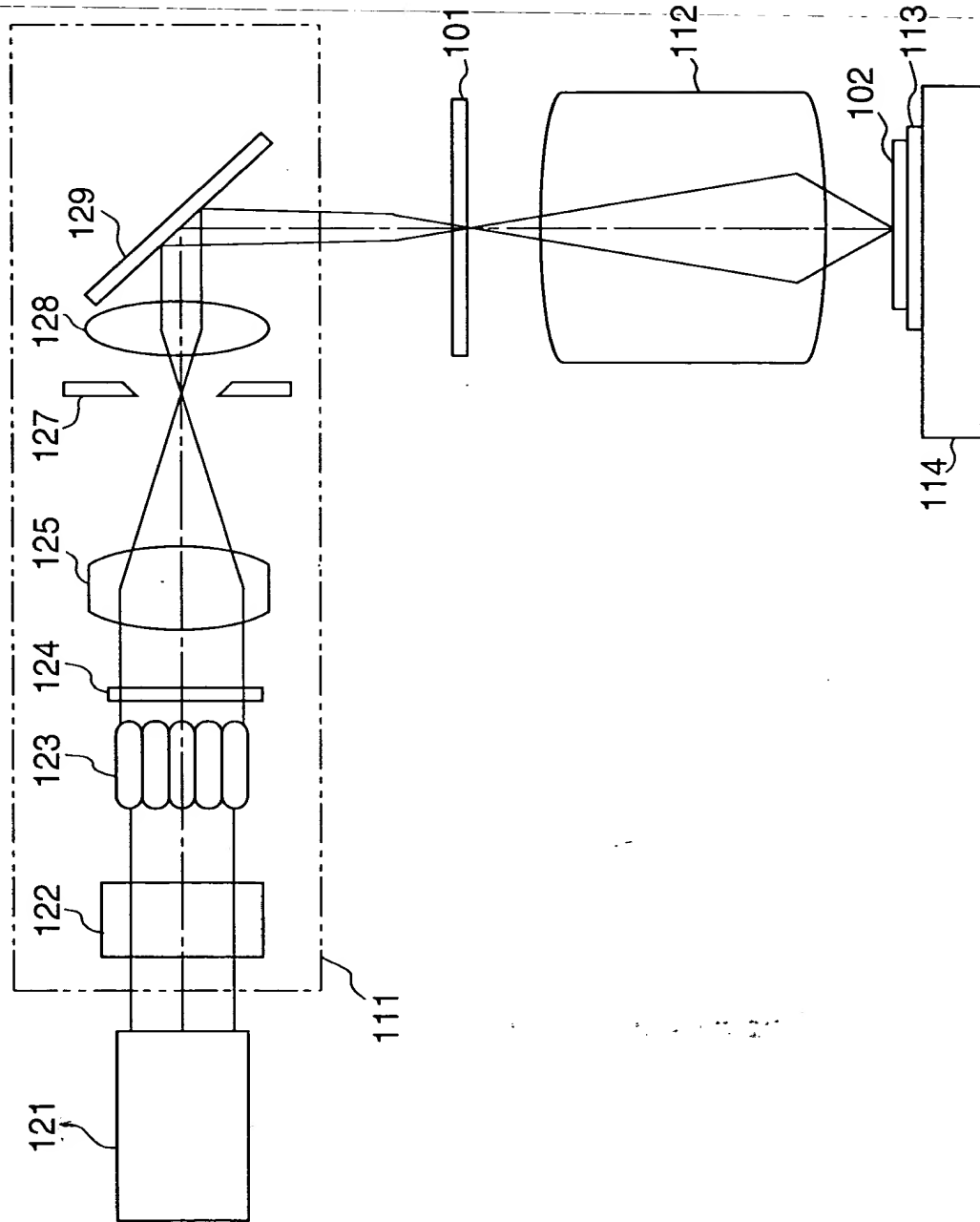
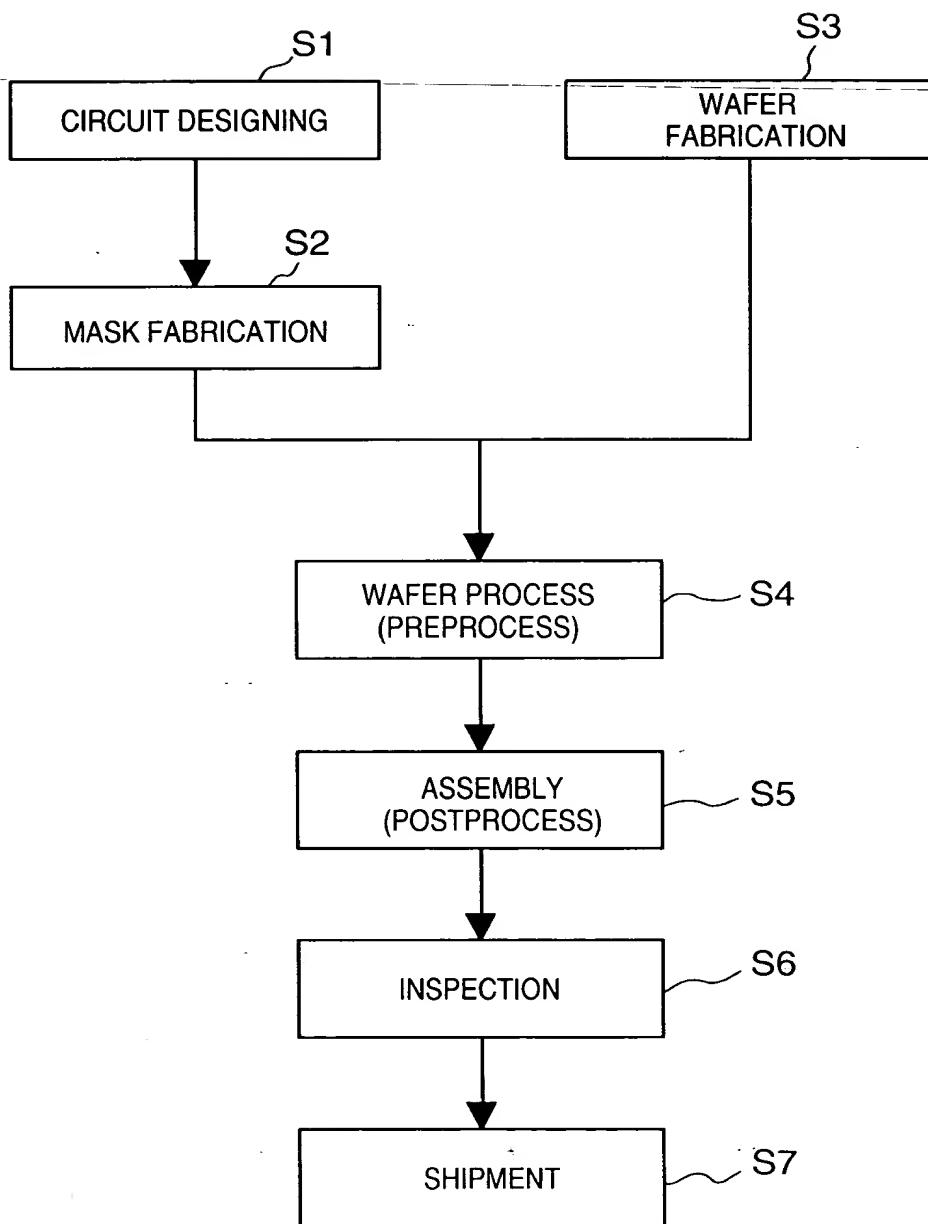
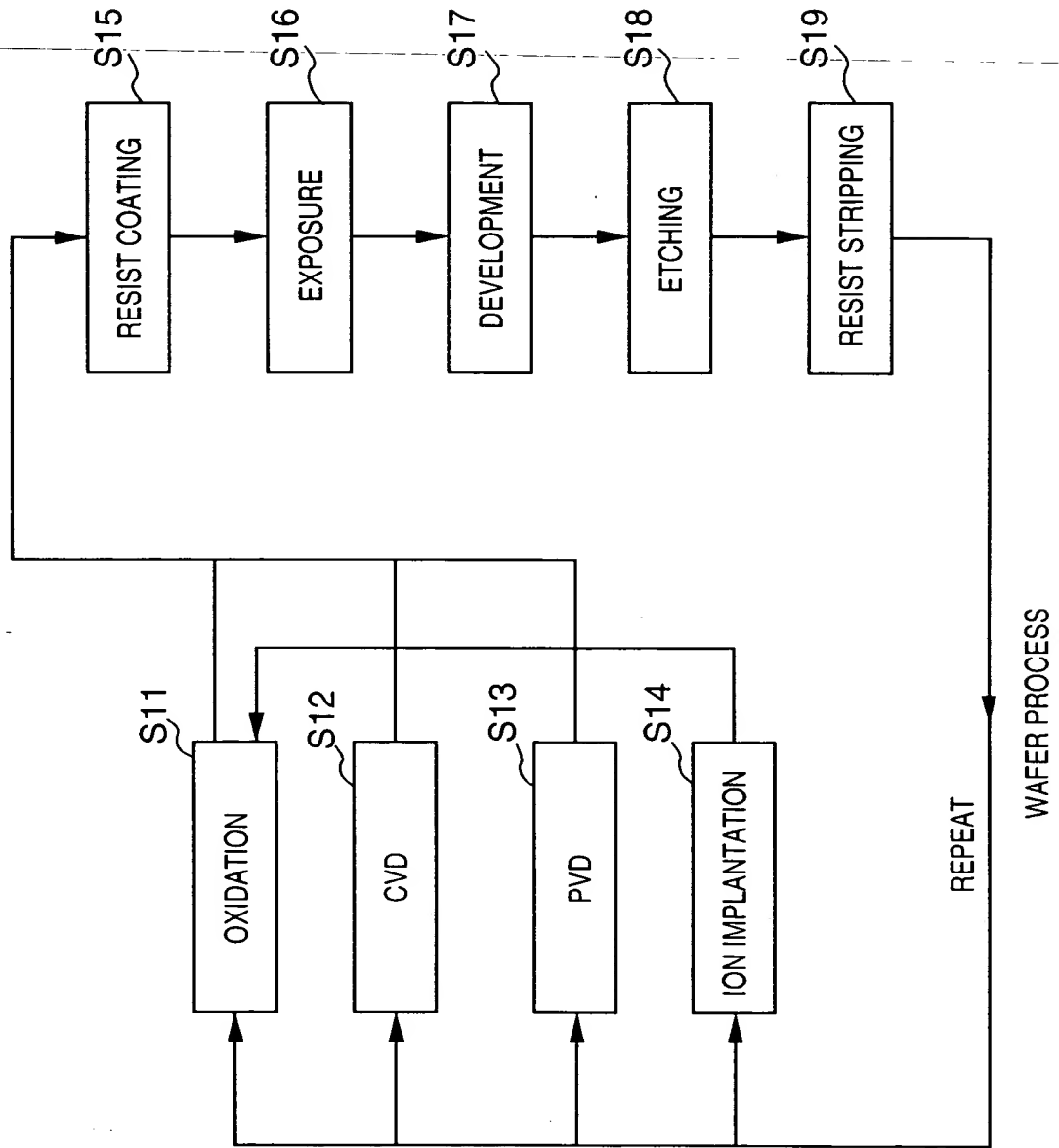


FIG. 7

SEMICONDUCTOR DEVICE FABRICATION FLOW

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FIG. 8

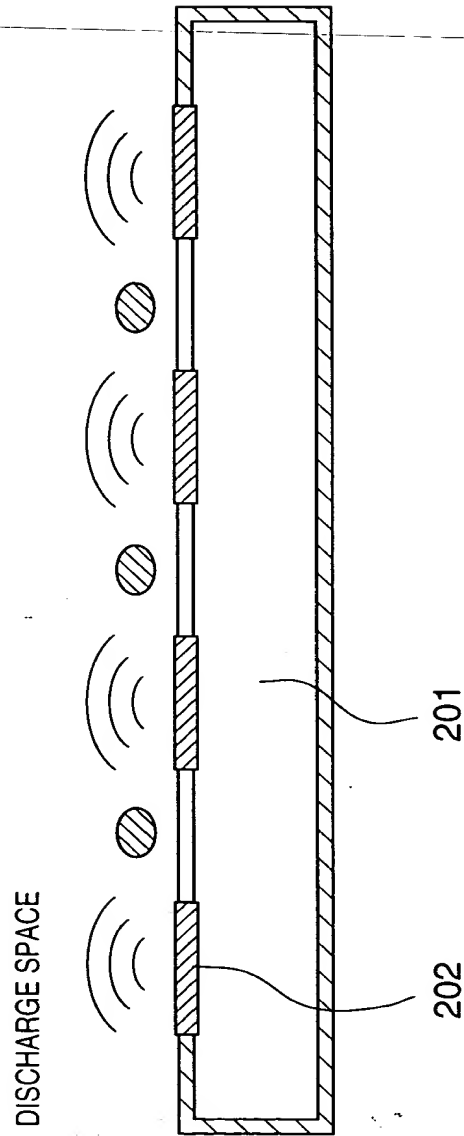


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BY	CLASS	SUBCLASS
DRAFTSMAN		

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FIG. 9



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